## AMENDMENTS TO THE SPECIFICATION

**Please replace the last paragraph bridging pages 3 and 4 with the following rewritten paragraph:**

The metal-polishing composition as described in Japanese Patent Application Laid-Open (Kokai) No. 8-837808-83980 containing benzotriazole effectively provides a flat surface and prevents dishing. However, polishing rate detrimentally decreases due to strong anti-corrosion effect of benzotriazole. The polishing composition as described in Japanese Patent Application Laid-Open (Kokai) No. 9-55363 containing 2-quinolinecarboxylic acid is not preferred for industrial use, since 2-quinolinecarboxylic acid is a remarkably expensive material.

**Please replace the sixth paragraph on page 7 with the following rewritten paragraph:**

[14] The polishing composition as recited in [12] or [13] above, wherein the surfactant is at least one species selected from the group consisting of an alkylaromatic-sulfonic acid or a salt thereof, polyoxyethylene alkyl phosphoric acid or a salt thereof, alkyl phophoric acid or a salt thereof, and a fatty acid or a salt thereof.

**Please replace the seventh paragraph on page 7 with the following rewritten paragraph:**

[15] The polishing composition as recited in any one of [12]to [14] above, wherein the content of the surfactant is in a range of 5 mass% or less.

**Please replace the first paragraph on page 8 with the following rewritten paragraph:**

[18] The polishing composition as recited in any one of [1] to [17] above, wherein the protective-film-forming agent comprises at least one species selected from the group consisting of benzotriazole, tolyltriazole, hydroxybenzotriazole, carboxybenzotriazole, benzimidazole, tetrazole, and quinaldinic acid.

**Please replace the second paragraph on page 8 with the following rewritten paragraph:**

[19] The polishing composition as recited in [18] ~~or [19]~~ above, wherein the content of the protective-film-forming agent is in a range of 10 mass % or less.

**Please replace the fifth paragraph on page 8 with the following rewritten paragraph:**

[22] The polishing composition as recited in [20] or [21] above, wherein the content of the alkali substance is in a range of 10 mass% or less.

**Please replace the eighth paragraph on page 8 with the following rewritten paragraph:**

[25] The polishing composition as recited in any one of [1] to [24] ~~[23]~~ above, wherein the content of the abrasive is in a range of 30 mass% or less.

**Please replace the last paragraph bridging pages 8 and 9 with the following rewritten paragraph:**

[28] The polishing composition as recited in any one of [1] to [27]~~[26]~~ above, wherein a ratio ($P_{RR}/B_{RR}$), between a metal film polishing rate ($P_{RR}$) for polishing a metal film formed on a substrate having trenches such that the metal film fills the trenches, or polishing a metal film formed on a substrate having trenches and a barrier metal film formed on the substrate such that the metal film fills the trenches, and a metal film polishing rate ($B_{RR}$) for polishing a flat blanket metal film, is 3.5 or more.

**Please replace the third full paragraph on page 9 with the following rewritten paragraph:**

[31] A polishing method comprising forming a metal film provided on the substrate having trenches such that the metal film fills the trenches, by use of the polishing composition as set forth in any one of [1] to [28]~~[27]~~ above.

**Please replace the fourth full paragraph on page 9 with the following rewritten paragraph:**

[32] A polishing method comprising forming a barrier metal film on a substrate having trenches, and polishing, by use of the polishing composition as recited in any one of [1] to [28]~~[27]~~ above, a metal film provided on the substrate such that the metal film fills the trenches.

**Please replace the fifth full paragraph on page 9 with the following rewritten paragraph:**

[33] A polishing method comprising a metal film, wherein a metal film formed on a substrate having trenches such that the metal film fills the trenches, or a metal film formed on a substrate having trenches and a barrier metal film formed on the substrate such that the metal

film fills the trenches, has protrusions, and corners of the protrusions are preferentially polished by the composition as set~~se t~~ forth in any one of [1] to [28]~~[27]~~ above.

**Please replace the third full paragraph on page 10 with the following rewritten paragraph:**

[37] The method for producing a substrate, the method comprising a step of polishing, through the polishing method as recited in any one of [31] to [33]~~[36]~~ above, a metal film provided on a substrate having trenches such that the metal film fills the trenches.

**Please replace the first full paragraph on page 29 with the following rewritten paragraph:**

Molecular weight of each of the synthesized compounds was determined through gel permeation chromatography (GPC) (reduced to polyethylene glycol). In the present invention, a commercial product was also employed, and molecular weight of the commercial product was also determined. The employed commercial product was VPI55K18P (hereinafter abbreviated as 18P) (1-vinylimidazole-1-vinylpyrrolidone (1:1) copolymer, product of BASF) and VPI55K72W (hereinafter abbreviated as 72W~~18P~~, product of BASF).

**Please replace the paragraph on page 42 with the following rewritten paragraph:**

The results are shown in Table 6. The rate of polishing tantalum barrier film decreased and erosion was more prevented, as increase in amount of azole 18P~~P18~~. However, since addition of 18P~~P18~~ in an excessive amount was prone to increase copper polishing rate, step reduction and dishing prevention effect tended to be impaired to degrees slightly higher than

those of Comparative Example 3 employing no 18P~~P18~~. Therefore, the amount of 18P~~P18~~ is required to be appropriately modified to attain well balance in the composition.

**Please replace the last paragraph bridging pages 50 and 51 with the following rewritten paragraph:**

DBS stands for dodecyl benzene sulphate, BTA benzotriazole, and THFA tetrahydrofurfuryl~~tetrahydrofrufryl~~ amine. The~~THe~~ colloidal silica used has a particle size of 70-80nm.

**Please replace Table 14 on page 56 with the following new Table 14:**

Table 14

| Ex. Com.Ex. | Polishing Pressure | Cu (blanket) polishing rate $B_{RR}$ | Cu (pattern) polishing rate $P_{RR}$ | $P_{RR}/B_{RR}$ | Step reduction | Dishing |
|---|---|---|---|---|---|---|
| Ex.32 | 14 kPa | 130 nm/min | 550 nm/min | 4.23 | AA | 50-60nm |
| Ex.33 | 10 kPa | 110 nm/min | 450 nm/min | 4.09 | AA | 40-60nm |
| Ex.34 | 20 kPa | 140 nm/min | 630 nm/min | 4.50 | AA | 70-80nm |